MwT-GX

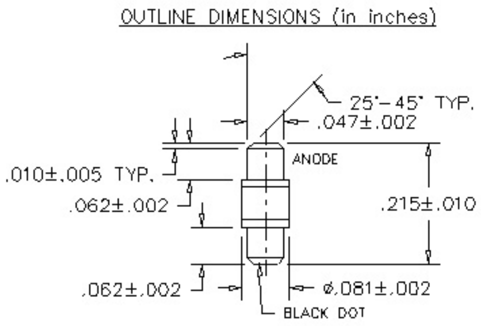
X-band 8-14 GHz Gunn Diode

Features:

- X-band (8-14 GHz) frequency source applications
- Excellent frequency chirp performance
- Pulsed or CW operation
- 20 years of proven performance & reliability
- Processed in MwT captive GaAs fab
- Available in packaged or die form

Typical Applications:

- Motion Detection and Surveillance
- Microwave Transmitter and Receiver
- Military Radar
- Gunn Diode Oscillators
- Radar Detectors



Based on MwT preparatory epitaxial profile design and process technology, MwT-GX is a Gunn diode device targeted at CW and pulsed X-band (8-14 GHz) frequency source applications. The device has output power of 15 dBm with excellent chirp performance in pulsed operation mode. The device is fabricated at MwT GaAs fab using process technologies with proven reliability and robustness. MwT-GX is available in die or packaged form.

Electrical Specifications @ T= +*25°C*

SYMBOL	PARAMETERS	Min	Typ	Max	Unit
Freq.	Frequency Range	8		14	GHz
P1dB	Output Power		15.0		dBm
	DC Voltage		8.0		V
Idd	DC Current		120		mA

Absolute Maximum Ratings

Maximum Bias Voltage	9.5 V
Maximum Case Operating Temperature	+ 85 °C
Maximum Storage Temperature	- 55 to + 120 °C

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